04 June 2003

Updated Search (Ph)

09/614,407

1 mone		Vipaula yaion cay	DB	Time stamp
L Number	Hits	Search Text	<del></del>	Time stamp 2003/06/03
-	83427	204/\$.ccls. or 205/\$.ccls.	USPAT;	15:47
. ]			US-PGPUB;	15:47
		,	EPO; JPO;	
		(004/4   005/4   )   //	DERWENT	2002/0//02
-	224	(204/\$.ccls. or 205/\$.ccls.) and ((prevention or	USPAT;	2003/06/02
		prevent or preventing or prevented or inhibit or	US-PGPUB;	14:19
		inhibition or inhibiting or inhibited or prohibit or	EPO; JPO;	
		prohibited or prohibiting) near (etch or etched or	DERWENT	
	_	etching))	110047	2002/04/00
-	2	(204/\$.ccls. or 205/\$.ccls.) and (((prevention or	USPAT;	2003/06/02
		prevent or preventing or prevented or inhibit or	US-PGPUB;	14:23
		inhibition or inhibiting or inhibited or prohibit or	EPO; JPO;	
		prohibited or prohibiting) near (etch or etched or	DERWENT	
		etching)) with seed)	LICDAT	2002/0//02
-	13	(204/\$.ccls. or 205/\$.ccls.) and (((prevention or	USPAT;	2003/06/02
		prevent or preventing or prevented or inhibit or	US-PGPUB;	14:25
		inhibition or inhibiting or inhibited or prohibit or	EPO; JPO;	
		prohibited or prohibiting) near (etch or etched or	DERWENT	,
		etching)) with (potential or voltage or current))	LICDAT	2003/04/03
-	695	(204/\$.ccls. or 205/\$.ccls.) and (cathodic adj	USPAT;	2003/06/02
		protection)	US-PGPUB;	14:26
			EPO; JPO;	
·	<b>.</b>	(1004/h l. 005/h l.) (/ .h./	DERWENT	2003/0//03
-	50	((204/\$.ccls. or 205/\$.ccls.) and (cathodic adj	USPAT;	2003/06/02
		protection)) and (semiconductor or wafer)	US-PGPUB;	14:28
•		,	EPO; JPO;	
		(204/4 la 205/4 ala) and (((aathada an	DERWENT	2003/06/02
-	771	(204/\$.ccls. or 205/\$.ccls.) and (((cathode or	USPAT;	15:53
		substrate or wafer or semiconductor) near	US-PGPUB; EPO; JPO;	19.95
		(immers\$3 or submer\$4 or lower\$3)) with (potential	DERWENT	
	10	or voltage or current))	USPAT;	2003/06/02
-	10	(204/\$.ccls. or 205/\$.ccls.) and (((cathode or	US-PGPUB;	14:55
		substrate or wafer or semiconductor) near (immers\$3 or submer\$4 or lower\$3)) with (potential	EPO; JPO;	17.55
		or voltage or current) with seed)	DERWENT	
	2	6432821.pn.	USPAT;	2003/06/02
]	۲.	0-10-2021.pm.	US-PGPUB;	15:08
		,	EPO; JPO;	10.00
			DERWENT	
_	3	("6245676"   "6297157"   "6340633"	USPAT	2003/06/02
-	,	"2002/0004301"   "2002/0022363").PN.		14:56
_	4	us-20020004301-\$.did. or us-20020022363-\$.did.	USPAT;	2003/06/02
	, T	22 222200 1001 4.0.2. 5. 80 2000000000 4.0.d.	US-PGPUB;	15:13
			EPO; JPO;	
			DERWENT	
_	4	4461680.pn. 6261433.pn.	USPAT;	2003/06/02
	]		US-PGPUB;	15:20
			EPO; JPO;	
			DERWENT	
<u> </u>	1	1999-582816.NRAN.	DERWENT	2003/06/02
	•	1,7,7, 0,3,0,0,0,0,0,0		15:18
		L	1	15.10

[ <del>-</del>	5	2882209.pn. 2742413.pn.	USPAT;	2003/06/02
			US-PGPUB;	15:20
			EPO; JPO;	
			DERWENT	
_	462	205/\$.ccls. and (((cathode or substrate or wafer or	USPAT;	2003/06/02
	.02	semiconductor) near (immers\$3 or submer\$4 or	US-PGPUB;	16:17
		lower\$3)) with (potential or voltage or current))	EPO; JPO;	
		i ional do ional de contraction de c	DERWENT	
_	2	6334419.pn.	USPAT;	2003/06/02
	-	000 1 122 .pm.	US-PGPUB;	15:54
			EPO; JPO;	
•			DERWENT	
_	79	(205/\$.ccls. and (((cathode or substrate or wafer or	USPAT;	2003/06/02
	'	semiconductor) near (immers\$3 or submer\$4 or	US-PGPUB;	16:17
		lower\$3)) with (potential or voltage or current))) and	EPO; JPO;	-5.5.
		(pulse or pulsing or pulsed)	DERWENT	
_	467	205/\$.ccls. and (((cathode or substrate or wafer or	USPAT;	2003/06/02
-	70/	semiconductor) near (immers\$3 or submer\$4 or	US-PGPUB;	16:17
		lower\$3)) with (potential or voltage or current or	EPO; JPO;	
		bias or biased or biasing))	DERWENT	
	.83	(205/\$.ccis. and (((cathode or substrate or wafer or	USPAT:	2003/06/02
-	.63	semiconductor) near (immers\$3 or submer\$4 or	US-PGPUB;	16:41
		lower\$3)) with (potential or voltage or current or	EPO; JPO;	10.71
	,	bias or biased or biasing))) and (pulse or pulsing or	DERWENT	
		pulsed)	DERWEIT	
	-5	205/\$.ccls. and ((immersion or entry) adj (voltage or	USPAT;	2003/06/02
-		bias or potential))	US-PGPUB;	16:49
		bias of potential))	EPO; JPO;	10117
			DERWENT	
	2	6162344.pn.	USPAT;	2003/06/03
-	_	0102377.pn.	US-PGPUB;	10:02
			EPO; JPO;	10.02
	•		DERWENT	
	72	205/105.ccls.	USPAT;	2003/06/03
_	'*		US-PGPUB;	12:06
	ł	·	EPO; JPO;	
			DERWENT	
	22	US-6551484-\$ or US-6074544-\$ or US-6432821-\$	USPAT;	2003/06/03
· .	""	or US-6340633-\$ or US-6245676-\$ or	US-PGPUB;	11:13
		US-6261433-\$ or US-6440291-\$ or US-6406611-\$	EPO	
*		or US-5595638-\$ or US-5348640-\$ or		
		US-4537663-\$ or US-6197179-\$ or US-6162344-\$		
		or US-6409903-\$).did. or (US-20030034250-\$ or		
		US-20020084189-\$ or US-20020074234-\$ or		
		US-20020084169-\$ or US-20020074234-\$ or US-20020015321-\$ or		,
		US-20020012964-\$ or US-20020011415-\$).did. or		
		(WO-9954527-\$).did.		
	1	[ (¥V Ο-330π0ε/-ψ).αια.	<u> </u>	J

-	1	((US-6551484-\$ or US-6074544-\$ or US-6432821-\$	USPAT;	2003/06/03
		or US-6340633-\$ or US-6245676-\$ or	US-PGPUB;	11:14
		US-6261433-\$ or US-6440291-\$ or US-6406611-\$	EPO; JPO;	
		or US-5595638-\$ or US-5348640-\$ or	DERWENT	
		US-4537663-\$ or US-6197179-\$ or US-6162344-\$		
		or US-6409903-\$).did. or (US-20030034250-\$ or		
		US-20020084189-\$ or US-20020074234-\$ or		
		U5-20020022363-\$ or U5-20010015321-\$ or		
		US-20020112964-\$ or US-20020011415-\$).did. or		
·		(WO-9954527-\$).did.) and strike	•	
_	148	205/\$.ccls. and (pulse or pulsed or pulsing) and seed	USPAT;	2003/06/03
		, , , , , , , , , , , , , , , , , , , ,	US-PGPUB;	14:17
			EPO; JPO;	
		•	DERWENT	
	32	205/\$.ccls. and ((high near (potential or voltage or	USPAT;	2003/06/03
		current)) with (strike or nucleation))	US-PGPUB;	14:19
			EPO; JPO;	
			DERWENT	
-	27	(204/\$.ccls. or 205/\$.ccls.) and (unitary or unified)	USPAT;	2003/06/03
		and (electroless with electroplating)	US-PGPUB;	15:50
		<u>'</u> ,	EPO; JPO;	
		·	DERWENT	
-	6	(204/\$.ccls. or 205/\$.ccls.) and (unitary or unified)	USPAT;	2003/06/03
		and (electroless with electroplating) and seed	'US-PGPUB;	15:49
		•	EPO; JPO;	
			DERWENT	
<b>-</b>	47	(204/\$.ccls. or 205/\$.ccls.) and system and (robot or	USPAT;	2003/06/03
		robotic) and (electroless with electroplating) and	US-PGPUB;	15:56
		seed .	EPO; JPO;	
			DERWENT	
-	12	(204/\$.ccls. or 205/\$.ccls.) and system and (robot or	USPAT;	2003/06/03
		robotic) and (electroless with electroplating) and	US-PGPUB;	16:05
		seed and (pulse or pulsed or pulsing)	.EPO; JPO;	
			DERWENT	
-	2	6277263.pn.	USPAT;	2003/06/03
			US-PGPUB;	16:47
			EPO; JPO;	
		•	DERWENT	